

*Handwritten signature*

COIL  
#2  
5-10-2



SMC-01-614

March 22, 2002

To: Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572  
20 McIntosh Drive  
Poughkeepsie, N.Y. 12603

RECEIVED  
APR 19 2002

TECHNOLOGY CENTER 095  
10/0559059

Subject:

Serial No. 10/0559059 01/23/02

Chuan-Chieh Huang et al.

METHOD TO IMPROVE VIA OR CONTACT  
HOLE PROFILE USING AN IN-SITU POLYMER  
DEPOSITION AND STRIP PROCEDURE

Grp. Art Unit: 2812

RECEIVED  
APR - 9 2002  
TECHNOLOGY CENTER 2800

RECEIVED  
MAY - 2 2002  
TECHNOLOGY CENTER 2800

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Statement  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner of Patents and  
Trademarks, Washington, D.C. 20231, on April 1, 2002.

Stephen B. Ackerman, Reg.# 37761

Signature/Date *SSD* 4/1/02

U.S. Patent 6,130,169 to Shields et al., "Efficient In-Situ Resist Strip Process for Heavy Polymer Metal Etch," discloses an in-situ resist strip process to remove polymer on the sidewalls. The 4th step uses a O<sub>2</sub> containing plasma.

U.S. Patent 5,925,577 to Solis, "Method for Forming Via Contact Hole in a Semiconductor Device," discloses a process to form and remove in-situ polymer from the sidewalls of via holes.

U.S. Patent 6,228,775 to Coburn et al., "Plasma Etching Method Using Low Ionization Potential Gas," discloses an etching method for forming an opening.

U.S. Patent 5,928,967 to Radens et al., "Selective Oxide-to-Nitride Etch Process Using C<sub>4</sub>F<sub>8</sub>/CO/AR," discloses a dry etch process for use in the fabrication of integrated circuits which use SiN etch stop layers.

U.S. Patent 6,232,237 to Tamaoka et al., "Method for Fabricating Semiconductor Device," discloses a method for fabricating a semiconductor device.

U.S. Patent 5,851,302 to Solis, "Method for Dry Etching Sidewall Polymer," discusses a method of plasma etching photoresist and sidewall polymer with an etch gas mixture.

TSMC-01-614

U.S. Patent 6,130,166 to Yeh, "Alternative Plasma Chemistry for Enhanced Photoresist Removal," discusses a method where a  $\text{CF}_4/\text{H}_2\text{O}_2$  plasma is used to remove residues remaining after an ashing step.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a long horizontal flourish extending to the right.

Stephen B. Ackerman,  
Reg. No. 37761

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.